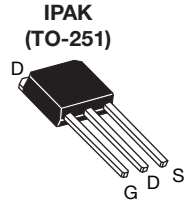
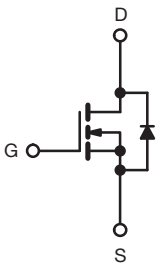
Power MOSFET





N-Channel MOSFET

FEATURES

- Straight lead
- Available in tape and reel
- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE Available

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

PRODUCT SUMMARY		
V_{DS} (V)	100	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.54
Q_g (Max.) (nC)	8.3	
Q_{gs} (nC)	2.3	
Q_{gd} (nC)	3.8	
Configuration	Single	

ORDERING INFORMATION	
Package	IPAK (TO-251)
Lead (Pb)-free and halogen-free	SiHFU110-GE3
Lead (Pb)-free	IRFU110PbF

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	100	V
Gate-source voltage			V_{GS}	± 20	
Continuous drain current	V_{GS} at 10 V	T_C = 25 °C	I_D	4.3	A
		T_C = 100 °C		2.7	
Pulsed drain current [a]			I_{DM}	17	
Linear derating factor				0.2	W/°C
Single pulse avalanche energy [b]			E_{AS}	75	mJ
Repetitive avalanche current [a]			I_{AR}	4.3	A
Repetitive avalanche energy [a]			E_{AR}	2.5	mJ
Maximum power dissipation	T_C = 25 °C		P_D	25	W
Peak diode recovery dV/dt [c]			dV/dt	5.5	V/ns
Operating junction and storage temperature range			T_J, T_{stg}	- 55 to + 150	°C
Soldering recommendations (peak temperature)	for 10 s			300 [d]	

Notes

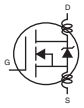
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. V_{DD} = 25 V, starting T_J = 25 °C, L = 8.1 mH, R_g = 25 Ω, I_{AS} = 4.3 A (see fig. 12)
c. $I_{SD} \leq 5.6$ A, dI/dt ≤ 75 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
d. 1.6 mm from case

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THERMAL RESISTANCE RATINGS					
PARAMETER	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	-	110	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	5.0	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	100	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.63	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V	-	-	25	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 125 °C	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V; I_D = 0.90 A[b]	-	-	0.54	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 0.90 A	1.1	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5	-	180	-	pF
Output Capacitance	C_{oss}		-	81	-	
Reverse Transfer Capacitance	C_{rss}		-	15	-	
Total Gate Charge	Q_g	V_{GS} = 10 V; I_D = 5.6 A, V_{DS} = 80 V, see fig. 6 and 13[b]	-	-	8.3	nC
Gate-Source Charge	Q_{gs}		-	-	2.3	
Gate-Drain Charge	Q_{gd}		-	-	3.8	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, I_D = 5.6 A, R_g = 24 Ω, R_D = 8.4 Ω, see fig. 10[b]	-	6.9	-	ns
Rise Time	t_r		-	16	-	
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	
Fall Time	t_f		-	9.4	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.0	-	nH
Internal Source Inductance	L_S		-	6.0	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	1.5	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	12	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 1.5 A, V_{GS} = 0 V[b]	-	-	2.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 5.6 A, dI/dt = 100 A/µs[b]	-	100	200	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.44	0.88	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

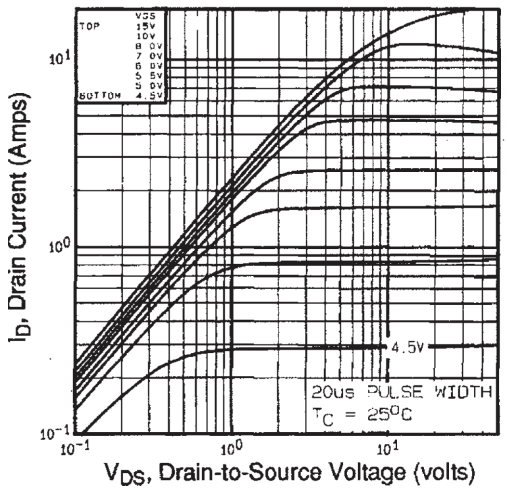


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

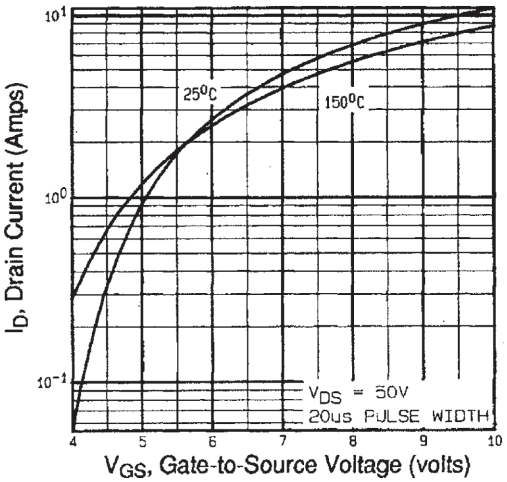


Fig. 2 - Typical Transfer Characteristics

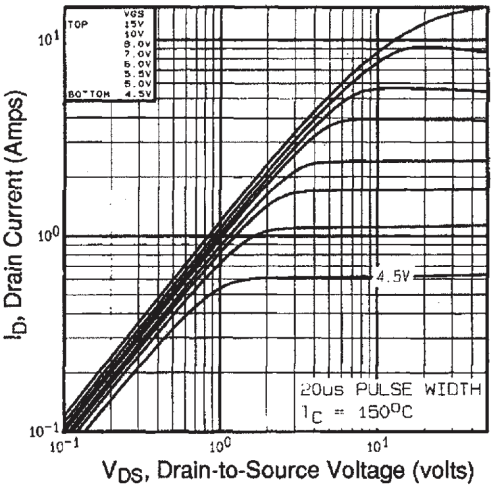


Fig. 1 - Typical Output Characteristics, T_C = 150 °C

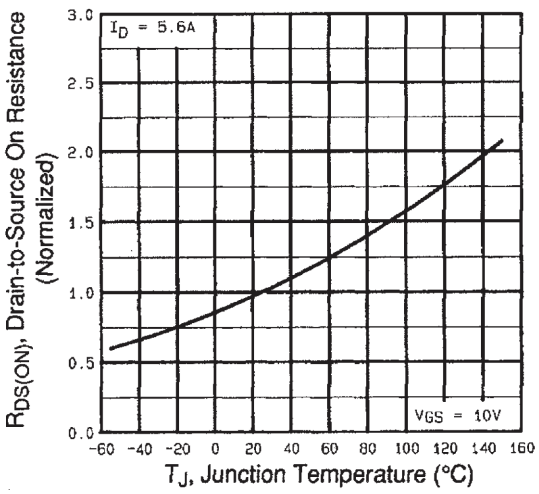


Fig. 3 - Normalized On-Resistance vs. Temperature

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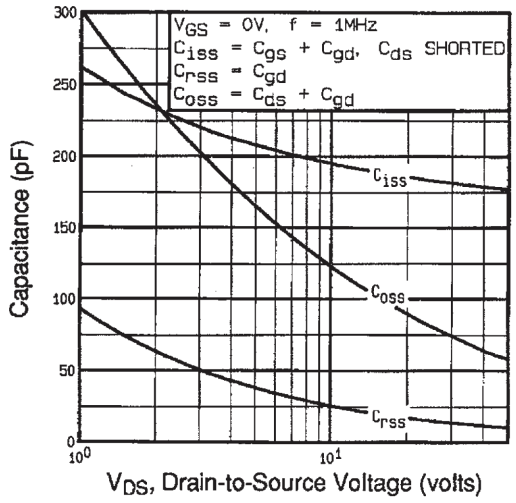


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

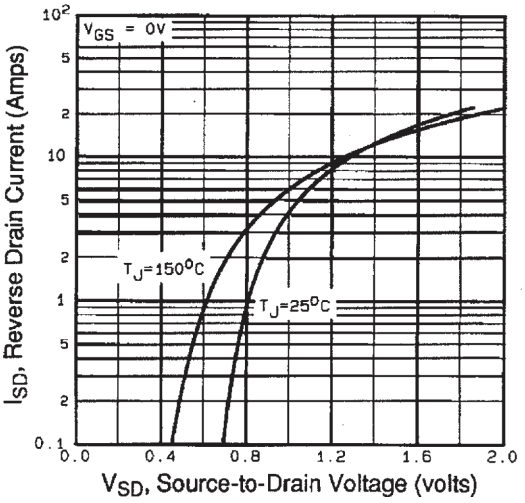


Fig. 6 - Typical Source-Drain Diode Forward Voltage

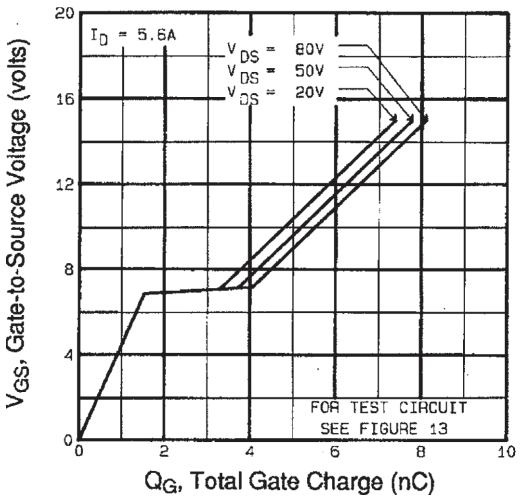


Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

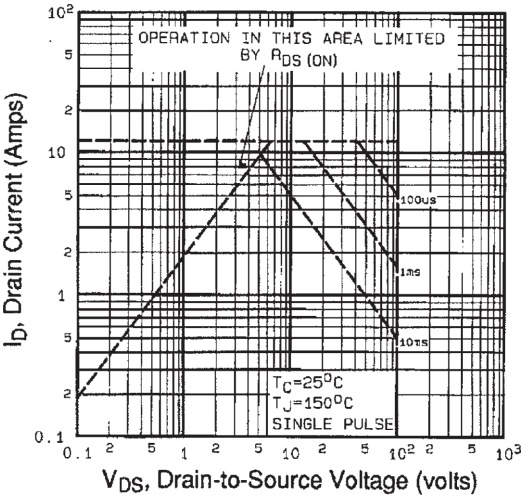


Fig. 7 - Maximum Safe Operating Area

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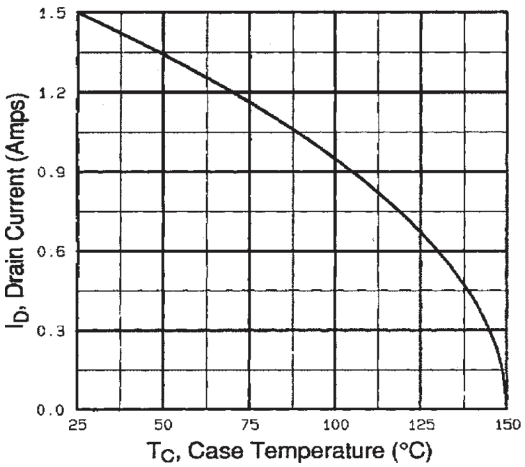


Fig. 8 - Maximum Drain Current vs. Case Temperature

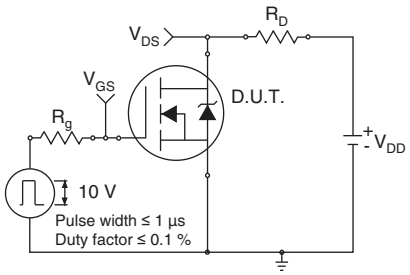


Fig. 10a - Switching Time Test Circuit

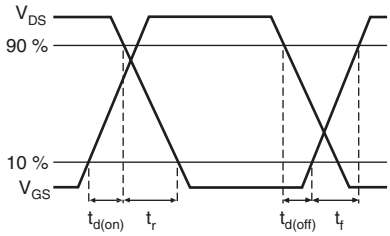


Fig. 10b - Switching Time Waveforms

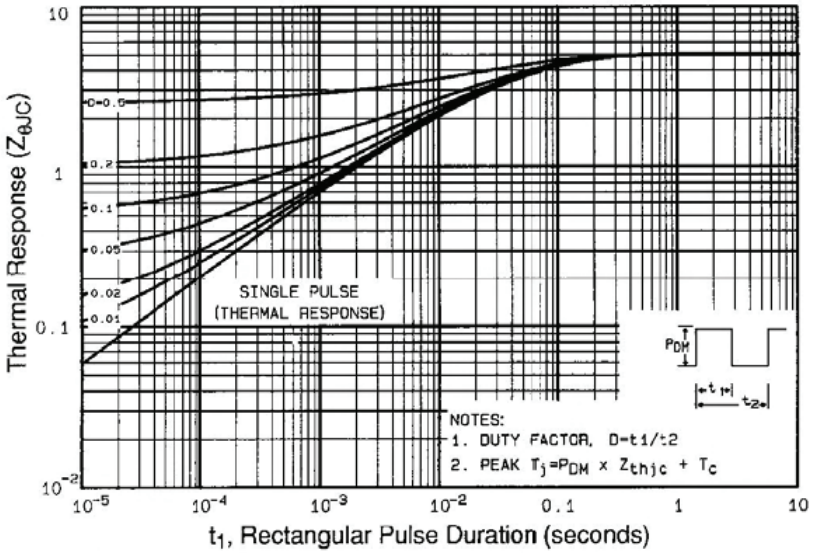


Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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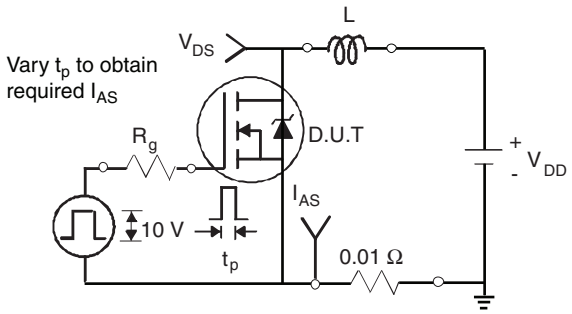


Fig. 12a - Unclamped Inductive Test Circuit

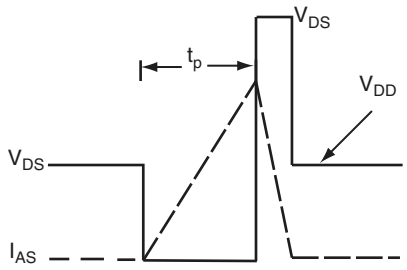


Fig. 12b - Unclamped Inductive Waveforms

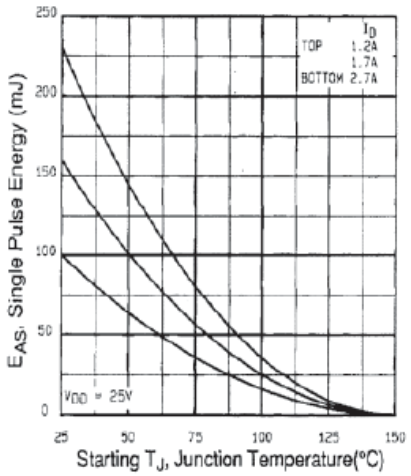


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

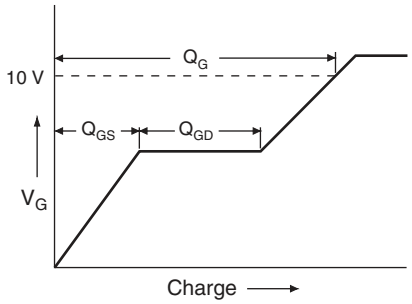


Fig. 13a - Basic Gate Charge Waveform

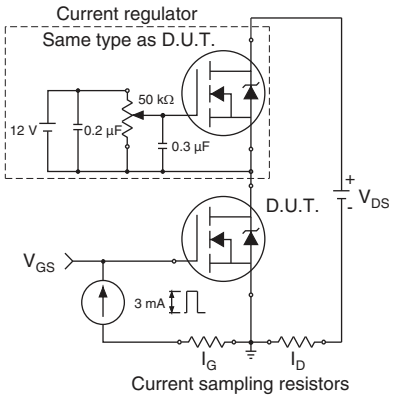
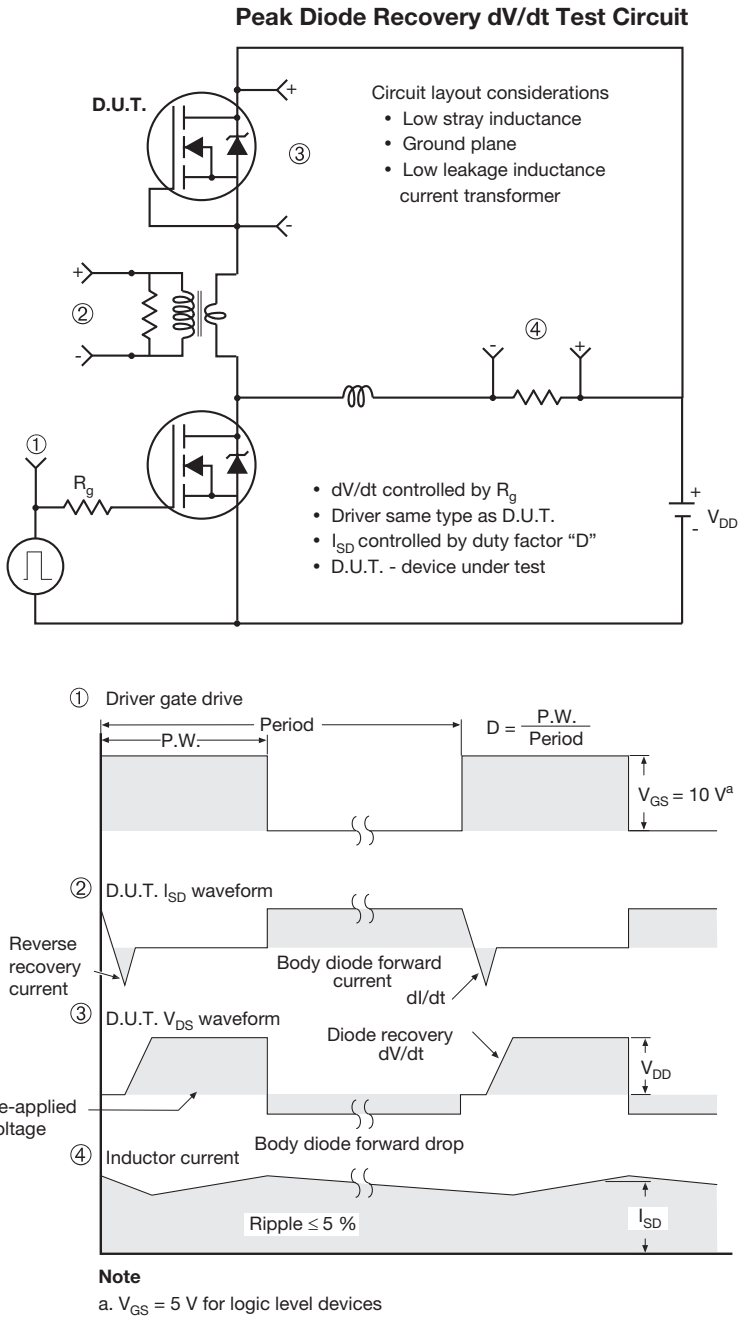


Fig. 13b - Gate Charge Test Circuit

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Note

a. V_{GS} = 5 V for logic level devices

Fig.14 - For N-Channel

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